

A cross-sectional view of a semiconductor device. It shows a substrate 11 with diagonal hatching. A layer 12 is formed on top of the substrate. On layer 12, there is a patterned layer 13a, which consists of a series of rectangular blocks 14. One specific block is labeled 14a. The blocks 14 are separated by gaps in the layer 13a.

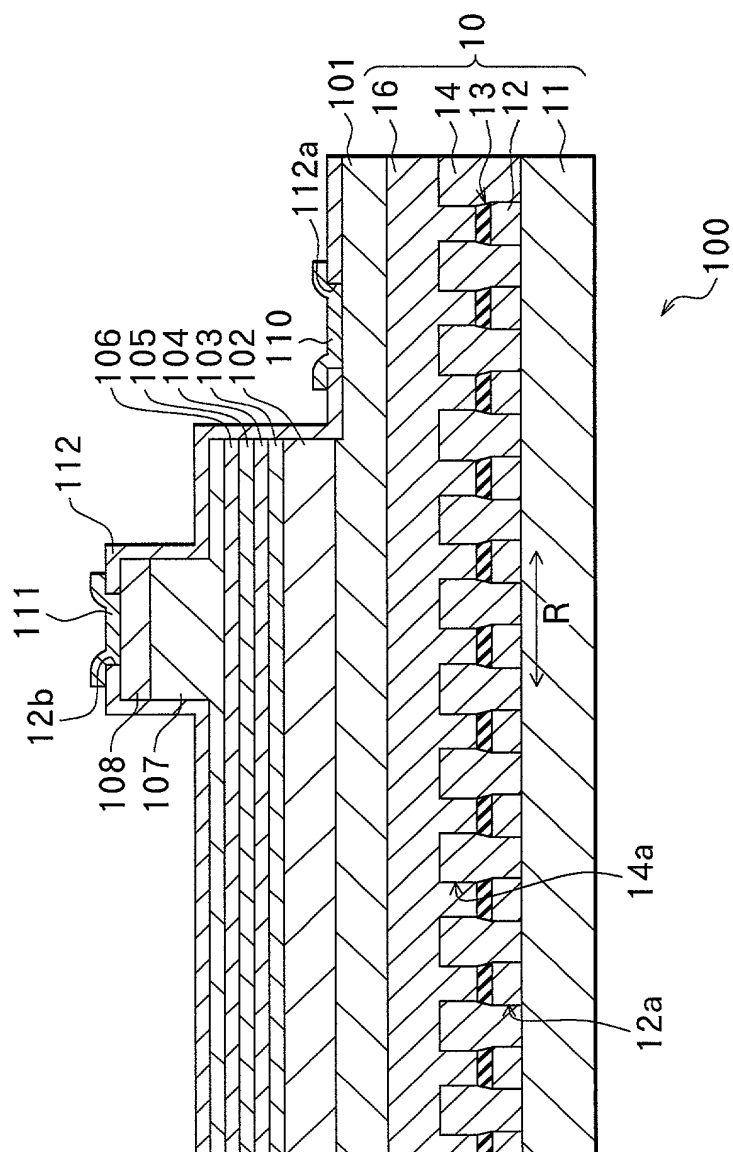
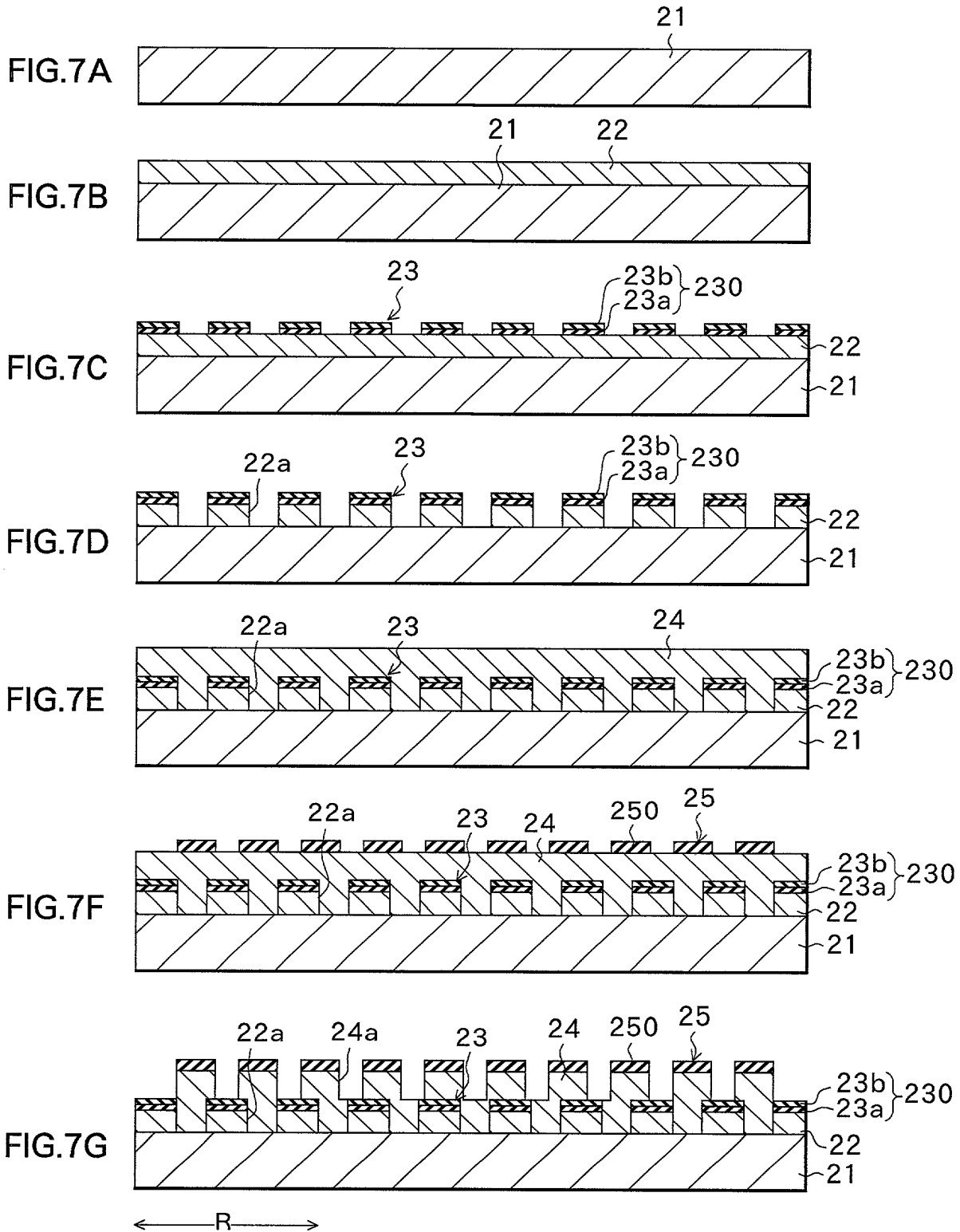


FIG. 3

A cross-sectional view of a semiconductor device. It shows a substrate 11 with diagonal hatching. Above the substrate is a layer 12. On top of layer 12 is a layer 13a, which contains a series of rectangular features 17. Above layer 13a is a layer 13b. The topmost layer is 14. The features 17 are shown with diagonal hatching, matching the substrate 11.

A cross-sectional view of a semiconductor device. It shows a series of repeating rectangular structures on a substrate 11. Each structure consists of a base layer 12, a middle layer 13a, and a top layer 13b. The top layer 13b is patterned into a series of ridges. The ridges are labeled 14 and 15, and the valleys between them are labeled 17. The middle layer 13a is also patterned into a series of ridges, which are labeled 13. The base layer 12 is a continuous layer underlying the patterned layers.





A cross-sectional view of a semiconductor device. It shows a substrate 21 at the bottom, followed by a layer 22. Above layer 22 is a layer 23a, which contains a series of rectangular blocks 22a. Above layer 23a is a layer 24, which contains a series of rectangular blocks 24a. The blocks 22a and 24a are arranged in a staggered pattern.

$$\longleftrightarrow R \longleftrightarrow$$

20



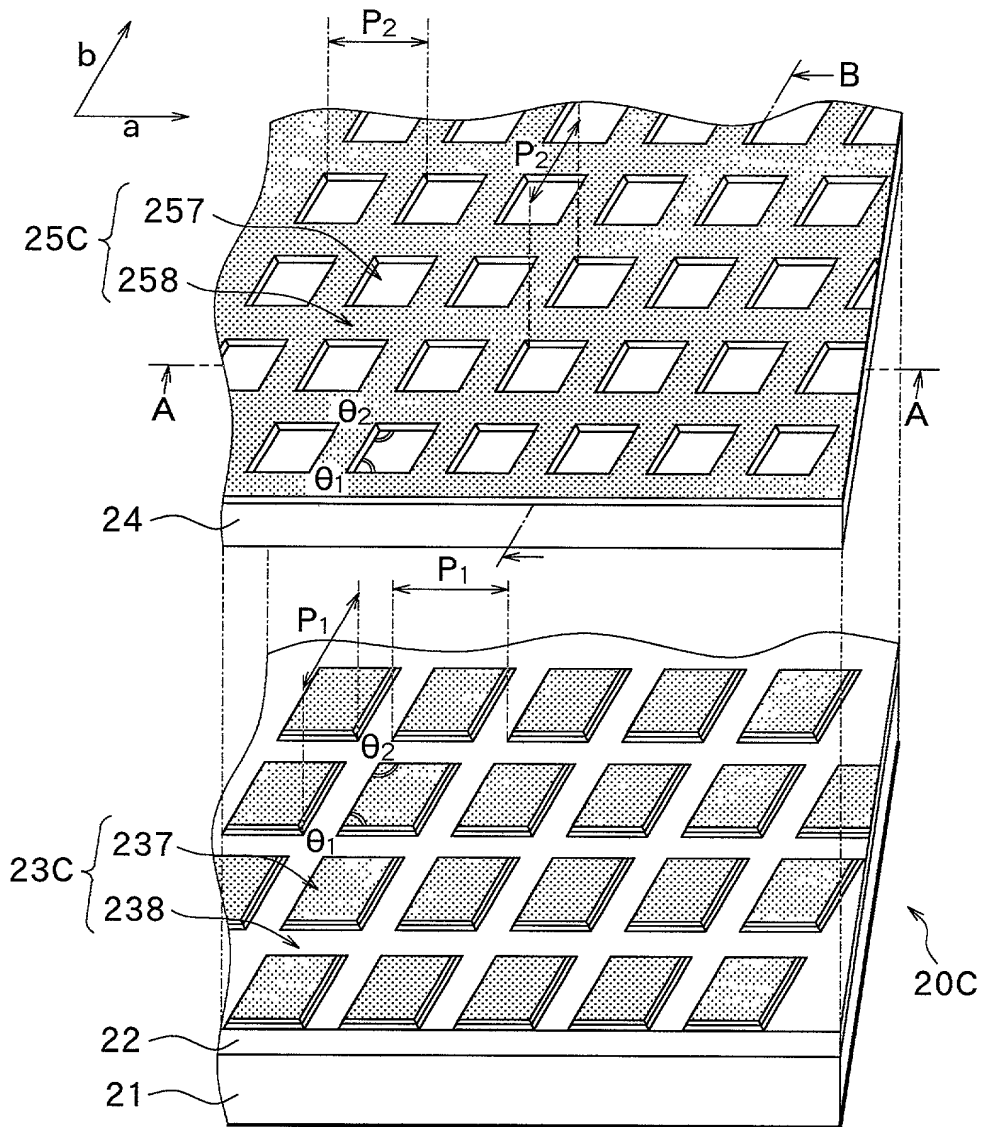


FIG.11

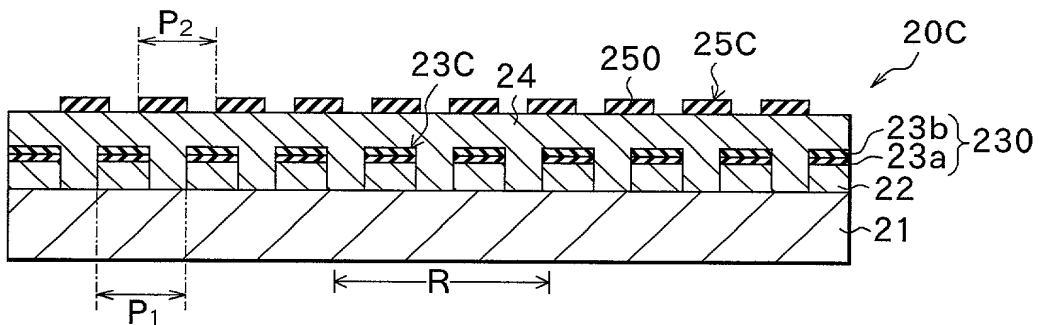


FIG.12